

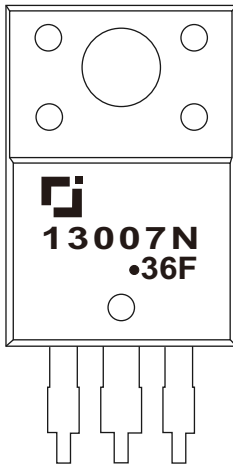
TO-220F Plastic-Encapsulate Transistor

3DD13007N36F TRANSISTOR (NPN)

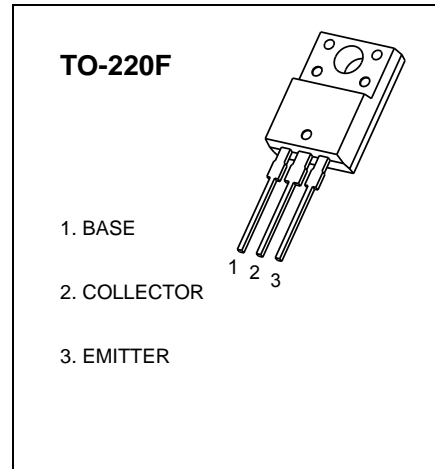
FEATURES

- Power switching applications

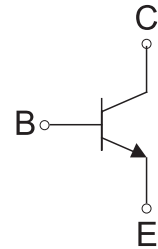
MARKING



13007N=Device code
 Solid dot=Green moldinn compound device,
 if none,the normal device
 36F=Code



Equivalent Circuit



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	700	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	9	V
I _C	Collector Current -Continuous	8	A
P _C	Collector Power Dissipation	2	W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Ma	
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 1mA, I _E =0	700			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	400			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =1mA, I _C =0	9			V
Collector cut-off current	I _{CBO}	V _{CB} =700V, I _E =0			100	μ A
Collector cut-off current	I _{CEO}	V _{CE} =400V, I _B =0			100	μ A
Emitter cut-off current	I _{EBO}	V _{EB} =9V, I _C =0			100	μ A
DC current gain	h _{FE(1)}	V _{CE} =5V, I _C =2A	10		40	
	h _{FE(2)}	V _{CE} =5V, I _C =8A	5			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =2A, I _B =0.4A			1	V
	V _{CE(sat)2}	I _C =5A, I _B =1A			2	V
	V _{CE(sat)3}	I _C =8A, I _B =2A			3	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _C =2A, I _B =0.4A			1.2	V
	V _{BE(sat)2}	I _C =5A, I _B =1A			1.6	V
Storage time	t _S	I _C =500mA (UI9600)	3		6	μ s
Fall time	t _f	I _C =500mA (UI9600)			0.5	μ s
Transition frequency	f _T	V _{CE} =10V, I _C =0.5A, f=1MHz	4			MHz

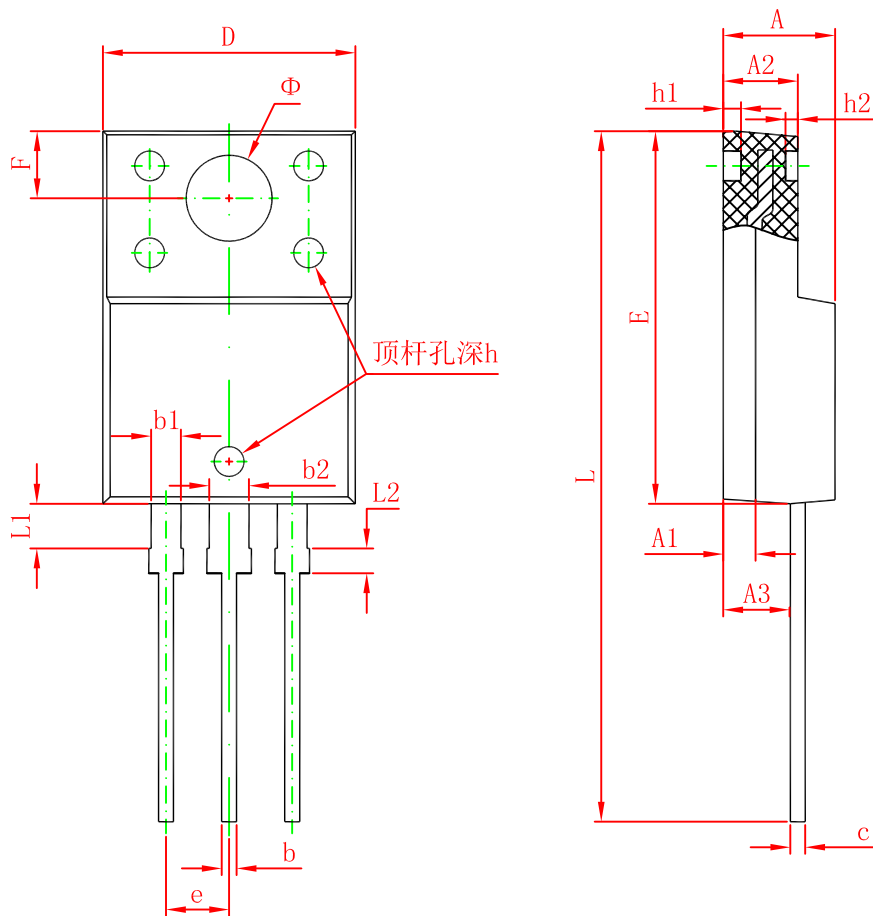
CLASSIFICATION OF h_{FE(1)}

Range	10-15	15-20	20-25	25-30	30-35	35-40

CLASSIFICATION OF t_S

Rank	A	B	C
Range	3-4(μ s)	4-5(μ s)	5-6(μ s)

TO-220F Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
A1	1.300 REF.		0.051 REF.	
A2	2.800	3.200	0.110	0.126
A3	2.500	2.900	0.098	0.114
b	0.500	0.750	0.020	0.030
b1	1.100	1.350	0.043	0.053
b2	1.500	1.750	0.059	0.069
c	0.500	0.750	0.020	0.030
D	9.960	10.360	0.392	0.408
E	14.800	15.200	0.583	0.598
e	2.540 TYP.		0.100 TYP.	
F	2.700 REF.		0.106 REF.	
Φ	3.500 REF.		0.138 REF.	
h	0.000	0.300	0.000	0.012
h1	0.800 REF.		0.031 REF.	
h2	0.500 REF.		0.020 REF.	
L	28.000	28.400	1.102	1.118
L1	1.700	1.900	0.067	0.075
L2	0.900	1.100	0.035	0.043

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - BJT category](#):

Click to view products by [Changjing Electronics Technology manufacturer](#):

Other Similar products are found below :

[BC559C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [NJVMJD148T4G](#) [NTE16](#) [NTE195A](#) [IMX9T110](#) [2N4401-A](#) [2N6728](#) [2SA1419T-TD-H](#) [2SB1204S-TL-E](#) [2SC5488A-TL-H](#) [FMC5AT148](#) [2N2369ADCSM](#) [2N2907A](#) [2N3904-NS](#) [2N5769](#) [2SC4618TLN](#) [CPH6501-TL-E](#) [US6T6TR](#) [BAX18/A52R](#) [BC556/112](#) [IMZ2AT108](#) [MMST8098T146](#) [MCH6102-TL-E](#) [BC846B-13-F](#) [2N3879](#) [30A02MH-TL-E](#) [NTE13](#) [NTE282](#) [NTE323](#) [NTE350](#) [NTE81](#) [JANTX2N2920L](#) [JANSR2N2907AUB](#) [CMLT3946EG TR](#) [SNSS40600CF8T1G](#) [CMLT3906EG TR](#) [GRP-DATA-JANS2N2907AUB](#) [GRP-DATA-JANS2N2222AUA](#) [MMDT3946FL3-7](#) [2N4240](#) [JANS2N3019](#) [MSB30KH-13](#) [2N2221AUB](#) [2SD1815T-TL-E](#) [2N6678](#) [2N2907Ae4](#) [JAN2N3507](#)